

isc Silicon NPN Power Transistor

2SC5387

DESCRIPTION

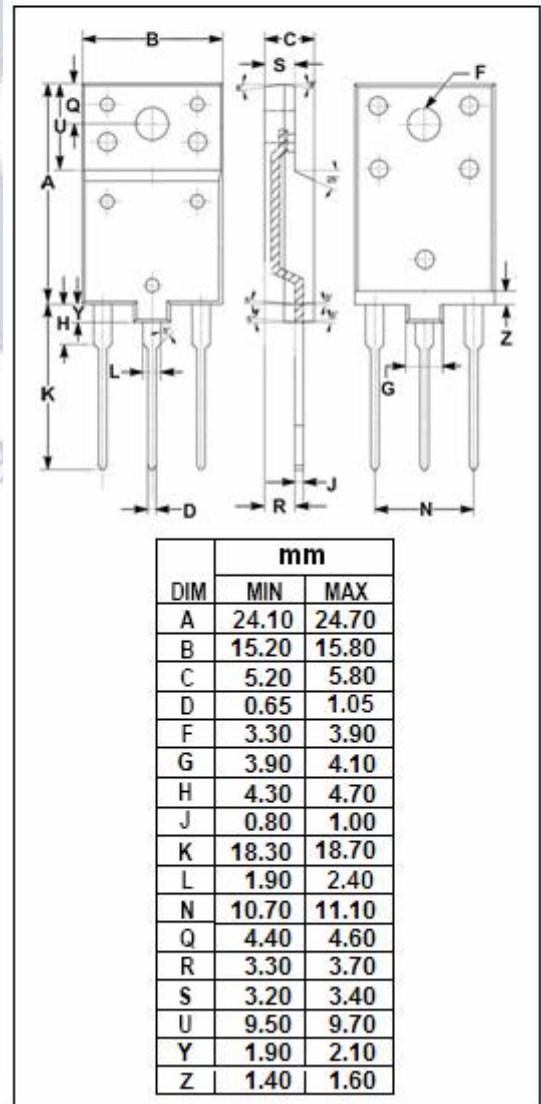
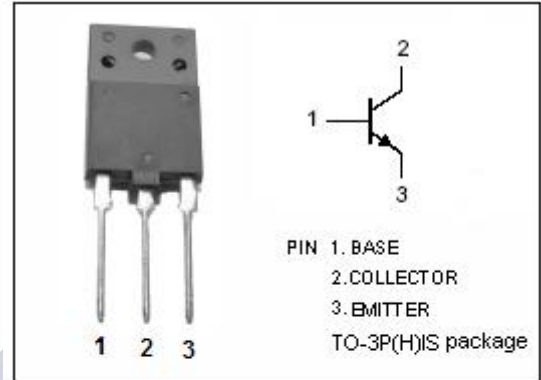
- High Breakdown Voltage-
: $V_{CBO} = 1200V$ (Min)
- High Switching Speed
- Low Saturation Voltage
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Horizontal deflection output for high resolution display, color TV.
- High speed switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1200	V
V_{CEO}	Collector-Emitter Voltage	600	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current- Continuous	10	A
I_{CM}	Collector Current- Pulse	20	A
I_B	Base Current- Continuous	5	A
P_C	Collector Power Dissipation @ $T_c=25^\circ C$	50	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



isc Silicon NPN Power Transistor**2SC5387****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; I _B = 0	600			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 8A; I _B = 2A			3.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 8A; I _B = 2A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 1200V; I _E = 0			1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			10	μA
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 5V	15		35	
h _{FE-2}	DC Current Gain	I _C = 8A; V _{CE} = 5V	4.3		7.8	
f _T	Current-Gain—Bandwidth Product	I _C = 0.1A; V _{CE} = 10V		1.7		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 1.0MHz		130		pF
t _{stg}	Storage Time			2.5	3.5	μs
t _f	Fall Time	I _{CP} = 6A, I _{B1(end)} = 1.2A; f _H = 64kHz		0.15	0.3	μs